

U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)				Docket No. APPM/6303.02	Serial No. 09/965,373			
<b>LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT</b>				Applicant Chung, et al.	Confirmation No.:			
COPY OF PAPERS ORIGINALLY FILED								
(Use several sheets if necessary)				Filing Date	Group			
		Examiner	Unknown TRADEMARK	September 26, 2001	Unknown			
<b>U.S. Patent Documents</b>								
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate	
WSL	A1	6,268,291	07-31-2001	Andricacos et al.	438	694	12-03-1998	
	A2	6,249,055	06-19-2001	Dubin	257	758	02-03-1998	
	A3	6,160,315	12-12-2000	Chiang et al.	257	762	01-06-2000	
	A4	6,066,892	05-23-2000	Ding et al.	257	751	05-14-1998	
	A5	6,037,257	03-14-2000	Chiang et al.	438	687	05-08-1997	
	A6	5,744,394	04-28-1998	Iguchi et al.	438	276	04-23-1997	
	A7	5,654,232	08-05-1997	Gardner	438	661	03-15-1996	
	A8							
	A9							
	A10							
	A11							
	A12							
<b>Foreign Patent Documents</b>								
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
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	B2						<input type="checkbox"/>	<input type="checkbox"/>
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	B5						<input type="checkbox"/>	<input type="checkbox"/>
<b>OTHER ART</b>								
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.						
WSL	C1	USSN 09/518,004, Filed March 2, 2000						
	C2							
	C3							
Examiner				Date Considered	8/26/03			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								

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U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)					Docket No. AMAT/6303.02/CPI/ COPPER/P02JS	Serial No. 09/965,373		
<b>LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT</b>					Applicant Chung, et al.			
(Use several sheets if necessary)					Filing Date September 26, 2001	Group Unknown		
Examiner Unknown								
<b>U.S. Patent Documents</b>								
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate	
WSL	A1	4,058,430	11/15/77	Suntola et al.	156	611	11/25/1978	
	A2	4,389,973	06/28/83	Suntola et al.	118	725	12/11/1981	
	A3	4,413,022	11/01/83	Suntola et al.	427	255.2	06/21/1979	
	A4	4,486,487	12/04/84	Skarp	428	216	04/25/1983	
	A5	4,767,494	08/30/88	Kobayashi et al.	156	606	09/19/1986	
	A6	4,806,321	02/21/89	Nishizawa et al.	422	245	07/21/1985	
	A7	4,829,022	05/09/89	Kobayashi et al.	437	107	12/09/1986	
	A8	4,834,831	05/30/89	Nishizawa et al.	156	611	09/04/1987	
	A9	4,838,983	06/13/89	Schumaker et al.	156	613	03/18/1988	
	A10	4,838,993	06/13/89	Aoki et al.	156	643	12/03/1987	
	A11	4,840,921	06/20/89	Matsumoto	437	89	06/30/1988	
	A12	4,845,049	07/04/89	Sunakawa	437	81	03/28/1988	
	A13	4,859,625	08/22/89	Nishizawa et al.	437	81	11/20/1987	
<b>Foreign Patent Documents</b>								
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
WSL	B1	01/66832 A2	09/13/2001	WO	C30B	16/44		X
	B2	01/40541 A1	06/07/2001	WO	C23C	16/40		X
	B3	01/36702 A1	05/25/2001	WO	C23C	16/00		X
	B4	01/29893 A1	04/26/2001	WO	H01L	21/768		X
	B5	01/29891 A1	04/26/2001	WO	H01L	21/768		X
<b>OTHER ART</b>								
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.						
WSL	C1	Hultman, et al., "Review of the thermal and mechanical stability of TiN-based thin films", Zeitschrift Fur Metallkunde, 90(10) (Oct. 1999), pp. 803-813.						
WSL	C2	Klaus, et al., "Atomic Layer Deposition of SiO <sub>2</sub> Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions", Surface Review & Letters, 6(3&4) (1999), pp. 435-448.						
Examiner <i>[Signature]</i>				Date Considered <i>8/26/03</i>				
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<b>LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT</b>					Applicant Chung, et al.			
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<b>U.S. Patent Documents</b>								
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate	
WSL	A14	4,859,627	08/22/89	Sunakawa	437	81	07/01/1988	
	A15	4,861,417	08/29/89	Mochizuki et al.	156	610	03/24/1988	
	A16	4,876,218	10/24/89	Pessa et al.	437	107	09/26/1988	
	A17	4,927,670	05/22/1990	Erbil	427	255.3	06/22/1988	
	A18	4,931,132	06/05/90	Aspnes et al.	156	601	10/07/1988	
	A19	4,960,720	10/02/90	Shimbo	437	105	08/24/1987	
	A20	4,975,252	12/04/90	Nishizawa et al.	422	245	05/26/1989	
	A21	4,993,357	02/19/91	Scholz	118	715	12/21/1989	
	A22	5,013,683	05/07/91	Petroff et al.	437	110	01/23/1989	
	A23	5,082,798	01/21/92	Arimoto	437	108	09/27/1990	
	A24	5,085,885	02/04/92	Foley et al.	477	38	09/10/1990	
	A25	5,091,320	02/25/92	Aspnes et al.	437	8	06/15/1990	
	A26	5,130,269	07/14/92	Kitahara et al.	437	111	04/25/1989	
	A27	5,166,092	11/24/92	Mochizuki et al.	437	105	10/30/1990	
<b>Foreign Patent Documents</b>								
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES      NO	
WSL	B6	01/29280 A1	04/26/2001	WO	C23C	16/32		X
	B7	01/27347 A1	04/19/2001	WO	C23C	16/44		X
	B8	01/27346 A1	04/19/2001	WO	C23C	16/44		X
	B9	01/15220 A1	03/01/2001	WO	H01L	21/768		X
<b>OTHER ART</b>								
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.						
WSL	C3	Yamaguchi, et al., "Atomic-layer chemical-vapor-deposition of silicon dioxide films with extremely low hydrogen content", <i>Appl. Surf. Sci.</i> , Vol. 130-132 (1998), pp. 202-207.						
WSL	C4	George, et al., "Surface Chemistry for Atomic Layer Growth", <i>J. Phys. Chem.</i> , Vol. 100 (1996), pp. 13121-131.						
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(Use several sheets if necessary)				Filing Date September 26, 2001	Group Unknown		
				Examiner Unknown			
<b>U.S. Patent Documents</b>							
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
WSL	A28	5,225,366	07/06/93	Yoder	437	108	06/22/1990
	A29	5,246,536	09/21/93	Nishizawa et al.	156	610	03/10/1989
	A30	5,250,148	10/05/93	Nishizawa et al.	156	611	11/12/1991
	A31	5,254,207	10/19/93	Nishizawa et al.	156	601	11/30/1992
	A32	5,256,244	10/26/93	Ackerman	156	613	02/10/1992
	A33	5,270,247	12/14/93	Sakuma et al.	437	133	07/08/1992
	A34	5,278,435	01/11/94	Van Hove et al.	257	184	06/08/1992
	A35	5,281,274	01/25/94	Yoder	118	697	02/04/1993
	A36	5,290,748	03/01/94	Knuutila et al.	502	228	07/16/1992
	A37	5,294,286	03/15/94	Nishizawa et al.	156	610	01/12/1993
	A38	5,296,403	03/22/94	Nishizawa et al.	437	133	10/23/1992
	A39	5,300,186	04/05/94	Kitahara et al.	156	613	04/07/1992
✓	A40	5,311,055	05/10/94	Goodman et al.	257	593	11/22/1991
<b>Foreign Patent Documents</b>							
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation
							YES
WSL	B10	00/79576 A1	12/28/2000	WO	H01L	21/205	X
	B11	00/79019 A1	12/28/2000	WO	C23C	16/00	X
✓	B12	00/63957 A1	10/26/2000	WO	H01L	21/205	X
<b>OTHER ART</b>							
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.					
WSL	C5	George, et al., "Atomic layer controlled deposition of SiO <sub>2</sub> and Al <sub>2</sub> O <sub>3</sub> using ABAB...binary reaction sequence chemistry", <i>Appl. Surf. Sci.</i> , Vol. 82/83 (1994), pp. 460-467.					
WSL	C6	Wise, et al., "Diethyldioctoxysilane as a new precursor for SiO <sub>2</sub> growth on silicon", <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 334 (1994), pp. 37-43.					
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<b>LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT</b>  (Use several sheets if necessary)				Applicant Chung, et al.	RECEIVED TECHNICAL DIVISION GROUP UNKNOWN		
	Examiner	Examiner	FEB 28 2002 PATENT & TRADEMARK OFFICE C-45	Filing Date September 26, 2001			
<b>U.S. Patent Documents</b>							
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
WSL	A41	5,316,615	05/31/94	Copel	117	95	03/09/1993
	A42	5,316,793	05/31/94	Wallace et al.	427	248.1	07/27/1992
	A43	5,330,610	07/19/94	Eres et al.	117	86	05/28/1993
	A44	5,336,324	08/09/94	Stall et al.	118	719	12/04/1991
	A45	5,338,389	08/16/94	Nishizawa et al.	117	89	04/21/1993
	A46	5,348,911	09/20/94	Jurgensen et al.	117	91	04/26/1993
	A47	5,374,570	12/20/94	Nasu et al.	437	40	08/19/1993
	A48	5,395,791	03/07/95	Cheng et al.	437	105	10/20/1993
	A49	5,438,952	08/08/1995	Otsuka	117	84	01/31/1994
	A50	5,439,876	08/08/95	Graf et al.	505	447	08/16/1993
	A51	5,441,703	08/15/95	Jurgensen	422	129	03/29/1994
	A52	5,443,033	08/22/95	Nishizawa et al.	117	86	03/11/1994
	A53	5,443,647	08/22/95	Aucoin et al.	118	723 ME	07/11/1994
↓	A54	5,455,072	10/03/95	Bension et al.	427	255.7	11/18/1992
<b>Foreign Patent Documents</b>							
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation
							YES      NO
WSL	B13	00/54320 A1	09/14/2000	WO	H01L	21/44	X
	B14	00/16377 A2	03/23/2000	WO	H01L	---	X
↓	B15	00/15881 A2	03/23/2000	WO	C30B	---	X
↓	B16	00/15865 A1	03/23/2000	WO	C23C	16/00	X
<b>OTHER ART</b>							
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.					
WSL	C7	Niinisto, et al., "Synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications", Mat. Sci. & Eng., Vol. B41 (1996), pp. 23-29.					
Examiner		Date Considered 8/26/03					
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<b>LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT</b>  (Use several sheets if necessary)				Applicant Chung, et al.	RECEIVED TECHNOLOGY PARK SEP 28 2002			
	Examiner WSL	Document Number Unknown	Issue Date Unknown	Filing Date September 26, 2001	Group Unknown			
<b>U.S. Patent Documents</b>								
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate	
WSL	A55	5,458,084	10/17/95	Thorne et al.	117	89	12/09/1993	
	A56	5,469,806	11/28/95	Mochizuki et al.	117	97	08/20/1993	
	A57	5,480,818	01/02/96	Matsumoto et al.	437	40	02/09/1993	
	A58	5,483,919	01/16/96	Yokoyama et al.	117	89	08/17/1994	
	A59	5,484,664	01/16/96	Kitahara et al.	428	641	01/21/1994	
	A60	5,503,875	04/02/96	Imai et al.	427	255.3	03/17/1994	
	A61	5,521,126	05/28/96	Okamura et al.	437	235	06/22/1994	
	A62	5,527,733	06/18/96	Nishizawa et al.	437	160	02/18/1994	
	A63	5,532,511	07/02/96	Nishizawa et al.	257	627	03/23/1995	
	A64	5,540,783	07/30/96	Eres et al.	118	725	05/26/1994	
	A65	5,601,651	02/11/97	Watabe	118	715	12/14/1994	
	A66	5,616,181	04/01/97	Yamamoto et al.	118	723 ER	11/21/1995	
↓	A67	5,637,530	06/10/97	Gaines et al.	114	105	06/10/1996	
<b>Foreign Patent Documents</b>								
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
WSL	B17	99/41423 A2	08/19/1999	WO	C23C	---		X
↓	B18	99/29924 A1	06/17/1999	WO	C23C	16/04		X
↓	B19	96/18756 A1	06/20/1996	WO	C23C	16/08		X
<b>OTHER ART</b>								
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.						
WSL	C8	Ritala, et al., "Perfectly conformal TiN and Al <sub>2</sub> O <sub>3</sub> films deposited by atomic layer deposition", <i>Chemical Vapor Deposition</i> , Vol. 5(1) (January 1999), pp. 7-9.						
WSL	C9	Klaus, et al., "Atomically controlled growth of tungsten and tungsten nitride using sequential surface reactions". <i>Appl. Surf. Sci.</i> , Vol 162-163 (2000), pp. 479-491.						
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(Use several sheets if necessary)					Filing Date September 26, 2001	Group Unknown		
Examiner Unknown					RECEIVED PTO 2001			
<b>U.S. Patent Documents</b>								
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate	
WSL	A68	5,641,984	06/24/97	Aftergut et al.	257	433	08/19/1994	
	A69	5,644,128	07/01/97	Wollnik et al.	250	251	08/25/1994	
	A70	5,693,139	12/02/97	Nishizawa et al.	117	89	06/15/1993	
	A71	5,705,224	01/06/98	Murota et al.	427	248.1	01/31/1995	
	A72	5,707,880	01/13/98	Aftergut et al.	437	3	01/17/1997	
	A73	5,711,811	01/27/98	Suntola et al.	118	711	11/28/1995	
	A74	5,730,802	03/24/98	Ishizumi et al.	118	719	12/27/1996	
	A75	5,747,113	05/05/98	Tsai	427	255.5	07/29/1996	
	A76	5,749,974	05/12/98	Habuka et al.	118	725	07/13/1995	
	A77	5,796,116	08/18/98	Nakata et al.	257	66	07/25/1995	
	A78	5,807,792	09/15/98	Ilg et al.	438	758	12/18/1996	
	A79	5,830,270	11/03/98	McKee et al.	117	106	08/05/1996	
	A80	5,835,677	11/10/98	Li et al.	392	401	10/03/1996	
<b>Foreign Patent Documents</b>								
*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
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	B21	93/02111 A1	02/04/1993	WO	C08F	4/78		X
	B22	91/10510 A1	07/25/1991	WO	B01J	37/02		X
	B23	0 799 641 A2	10/08/1997	EP	B01J	20/32		X
<b>OTHER ART</b>								
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WSL	C10	Min, et al., "Atomic layer deposition of TiN thin films by sequential introduction of Ti precursor and NH <sub>3</sub> ", Symp.: Advanced Interconnects and Contact Materials and Processes for Future Integrated Circuits (Apr. 13-16, 1998), pp. 337-342.						
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LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT <i>FEB 28 2002 PTO &amp; TRADEMARK OFFICE 545</i>				Applicant Chung, et al.		
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Examiner Unknown						
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*Examiner Initial	Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
WSL	A81 5,851,849	12/22/98	Comizzoli et al.	438	38	05/29/1997
	A82 5,855,675	01/05/99	Doering et al.	118	719	03/03/1997
	A83 5,855,680	01/05/99	Soininen et al.	118	719	11/28/1995
	A84 5,858,102	01/12/99	Tsai	118	719	02/14/1998
	A85 5,879,459	03/09/99	Gadgil et al.	118	715	08/29/1997
	A86 5,904,565	05/18/1999	Nguyen, et al.	438	687	07/17/1997
	A87 5,916,365	06/29/99	Sherman	117	92	08/16/1996
	A88 5,923,056	07/13/99	Lee et al.	257	192	03/12/1998
	A89 5,923,985	07/13/99	Aoki et al.	438	301	01/14/1997
	A90 5,925,574	07/20/99	Aoki et al.	437	31	04/10/1992
	A91 5,942,040	08/24/99	Kim et al.	118	726	08/27/1997
	A92 5,947,710	09/07/1999	Cooper, et al.	418	63	06/16/1997
	A93 5,972,430	10/26/99	DiMeo, Jr. et al.	427	255.32	11/26/1997
<b>Foreign Patent Documents</b>						
*Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation
						YES
WSL	B24 0 442 290 A1	02/14/1991	EP	C30B	25/02	X
	B25 0 344 352 A1	06/03/1988	EP	H01L	39/24	X
	B26 62-091495 A	04/25/1987	JP	C30B	25/02	X
<b>OTHER ART</b>						
*Examiner Initial	Including Author, Title, Date, Pertinent Pages, Etc.					
WSL	C11	Klaus, et al., "Atomic Layer Deposition of Tungsten using Sequential Surface Chemistry with a Sacrificial Stripping Reaction," Thin Solid Films 360 (2000), Pages 145 – 153, (Accepted Nov. 16, 1999).				
WSL	C12	Min, et al., "Metal-Organic Atomic-Layer Deposition of Titanium-Silicon-Nitride Films", Applied Physics Letters, American Inst. Of Physics, Vol 75(11) (Sept. 13, 1999).				
Examiner	<i>[Signature]</i>			Date Considered	8/26/03	
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	Examiner Unknown		RECEIVED INT'L MAY 2003

#### U.S. Patent Documents

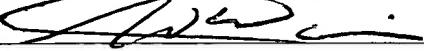
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
WSL	A94	6,001,669	12/14/99	Gaines et al.	438	102	07/21/1992
	A95	6,015,590	01/18/00	Suntola et al.	427	255.23	11/28/1995
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	A98	6,042,652	03/28/00	Hyun et al.	118	719	09/07/1999
	A99	6,043,177	03/28/00	Falconer et al.	502	4	01/21/1997
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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
WSL	B27	60-065712 A	04/15/1985	JP	C01B	33/113		X
	B28	03-048421	03/01/1991	JP	H01L	21/302		X
✓	B29	03-286531	12/17/1991	JP	H01L	21/316		X

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WSL	C13	Martensson, et al., "Atomic Layer Epitaxy of Copper on Tantalum", <i>Chemical Vapor Deposition</i> , 3(1) (Feb. 1, 1997), pp. 45-50.
↓	C14	Ritala, et al. "Atomic Layer Epitaxy Growth of TiN Thin Films", <i>J. Electrochem. Soc.</i> , 142(8) (Aug. 1995), pp. 2731-737.
↓	C15	Elers, et al., "NbC15 as a precursor in atomic layer epitaxy", <i>Appl. Surf. Sci.</i> , Vol. 82/83 (1994), pp. 468-474.

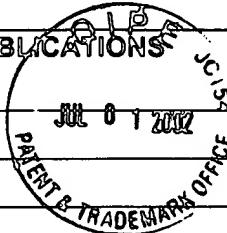
Examiner  Date Considered  8/26/03

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U.S. Department of Commerce Patent and Trademark Office (PTO Form 1449 modified)				Docket No.	Serial No.			
				AMAT/6303.02/CPI/ C45	09/965,373			
<b>LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT</b>				Applicant	RECEIVED TECHNOLOGY CENTER FAR-1 SEP 26 2001			
(Use several sheets if necessary)				Filing Date	Group Unknown			
				September 26, 2001	Unknown			
<b>U.S. Patent Documents</b>								
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate	
<i>WSL</i>	A106	6,200,893	03/13/2001	Sneh	438	685	03/11/1998	
	A107	6,203,613	03/20/2001	Gates, et al.	117	104	10/19/1999	
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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
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	B31	06-291048	10/18/1994	JP	H01L	21/205		X
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<i>WSL</i>	C16	Lee, "The Preparation of Titanium-Based Thin Film by CVD Using Titanium Chlorides as Precursors", <i>Chemical Vapor Deposition</i> , 5(2) (Mar. 1999), pp. 69-73.						
<i>WSL</i>	C17	Martensson, et al., "Atomic Layer Epitaxy of Copper, Growth & Selectivity in the Cu (II)-2,2,6,6-Tetramethyl-3, 5-Heptanedion ATE/H <sub>2</sub> Process", <i>J. Electrochem. Soc.</i> , 145(8) (Aug. 1998), pp. 2926-2931.						
Examiner	<i>[Signature]</i>			Date Considered	<i>8/26/03</i>			
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<b>LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT</b>				Applicant Chung, et al.			
(Use several sheets if necessary)				Filing Date September 26, 2001	Group Unknown	RECEIVED TECHNOLGY 8/26/03	
Examiner Unknown							
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*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
WSL	A118	2001/0011526	08/09/2001	Doering, et al.	118	729	01/16/2001
↓	A119	2001/0031562	10/18/2001	Raaijmakers, et al.	438	770	02/22/2001
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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation
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↓	B35	198 20 147	07/01/1999	DE	H01L	21/3205	X
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↓	C19	Bedair, "Atomic layer epitaxy deposition processes", J. Vac. Sci. Technol. 12(1) (Jan/Feb 1994)					
↓	C20	Yamaga, et al., "Atomic layer epitaxy of ZnS by a new gas supplying system in a low-pressure metalorganic vapor phase epitaxy", J. of Crystal Growth 117 (1992), pp. 152-155					
↓	C21	Elam, et al., "Nucleation and growth during tungsten atomic layer deposition on SiO <sub>2</sub> surfaces," Thin Solid Films 386 (2001) Pages 41 – 52, (Accepted Dec. 14, 2000).					
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<b>SUPPLEMENTAL LIST OF PATENTS AND PUBLICATIONS CITED BY APPLICANT</b>					Applicant Chung, et al.	Confirmation No. 6509
(Use several sheets if necessary)					Filing Date 09/26/2001	Group 2812
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*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
WS	A1	2001/0042799	11/22/2001	Kim, et al.	239	553	02/02/2001
	A2						
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	A13						

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**Foreign Patent Documents**

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**OTHER ART**

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C1	
	C2	
	C3	

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